



Attorney's Docket No. 42390P5778D

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Krishna Seshan; M. Lawrence A. Dass; and
Geoffrey L. Bakker

Serial No. 10/013,103

Filed: November 6, 2001

For: *Semiconductor Passivation Deposition Process
for Interfacial Adhesion (Amended)*

Examiner: Lewis, Monica

Art Unit: 2822

Confirmation No.: 1577

AMENDMENT AND RESPONSE TO FINAL OFFICE ACTION

Mail Stop AF
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Please amend the application as follows and consider the remarks which follow

IN THE CLAIMS

Please amend the claims as follows:

17. (Twice Amended) An integrated circuit (IC) comprising:
- an oxide layer;
 - an adhesion layer formed on said oxide layer; and
 - a first passivation layer formed on said adhesion layer, said first passivation layer and said adhesion layer including at least one common chemical element.

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